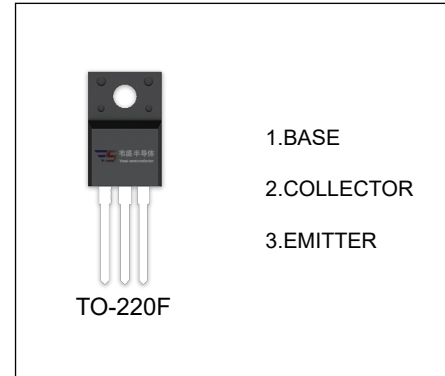


KTC4369 TRANSISTOR (NPN)

FEATURES

- High Transition Frequency
- Good Linearity of h_{FE}
- General Purpose Application



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	62.5	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	70		240	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=2.5\text{A}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			0.8	V
Base-emitter voltage	V_{BE}	$V_{CE}=2\text{V}, I_C=500\text{mA}$			1	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		35		pF
Transition frequency	f_T	$V_{CE}=2\text{V}, I_C=500\text{mA}$		100		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	70-140	120-240